

FEATURES

# 9V, 8A高效异步升压转换器

## 9V,8A Non-Synchronous Boost Converter

#### Input voltage range V<sub>IN</sub>: 2.5V to 8.5V ·输入电压范围VIN: 2.5V-8.5V Output voltage range V<sub>OUT</sub>: V<sub>IN</sub> to 9V · 输出电压范围Vout: V<sub>IN</sub>-9V Internal Fixed PWM Frequency: 650kHz ·内置固定开关频率:650kHz Internal 60mΩ, 8A power MOSFET · 内置60mΩ, 8A功率开关管 High Efficiency · 高转换效率: 87% (V<sub>IN</sub> = 3.7V, V<sub>OUT</sub>=7.5V, I<sub>OUT</sub> =1A) 87% (V<sub>IN</sub> = 3.7V, V<sub>OUT</sub>=7.5V, I<sub>OUT</sub> =1A) Adjustable Current Limitation ·限流保护功能,外部可调节 Output overvoltage protection (at 9.5V), thermal ·输出过压 (9.5V)、热关断等保护 shutdown protection ·SOP8L-PP,无铅封装 Pb-free Packages, SOP8L-PP APPLICATIONS ・无线音响 • 便携式音箱 Smart Speakers Wireless Speakers 智能音响 Portable Speakers E-Cigarette ・电子烟 · 移动电源 · 拉杆音箱 Power bank Outdoor Speakers ORDERING INFORMATION

Part Number	Package Type	Marking	Operating Temperature Range	MOQ/Shipping Package
HT8905SPER	SOP8L-PP	HT8905sp UVWXYZ <sup>1</sup>	-40℃~85℃	Tape and Reel 3000PCS
HT8905SPET	SOP8L-PP	HT8905sp UVWXYZ	-40℃~85℃	Tube 100PCS

## TYPICAL APPLICATION



<sup>1</sup> UVWXYZ is production tracking code



#### DESCRIPTION

The HT8905 is a non-synchronous boost converter integrated with a  $60m\Omega$  power switch to provide a high efficiency and small size solution in portable systems.

The HT8905 has an input voltage range from 2.5 V to 8.5V to support applications with single cell and two cell Lithium batteries. The device has 8A switch current capability and can provide an output voltage up to 9V.

A function of adjustable Current limitation is available to protect HT8905 from over current during operation, and to prevent the battery from being over-pulled caused by an overload.

The HT8905 is available in SOP8L-PP, with very limited external components, so that it provides space-saving PCB for various applications.

The HT8905 provides 9.5V output overvoltage protection, and thermal shutdown protection.

HT8905是一款采用CMOS工艺的升压转换器, 内部集成了60mΩ,8A功率开关管。

HT8905具有2.5V至8.5V的输入电压范围,可 为采用单节或两节锂电池的应用提供支持。该 器件具备8A开关电流能力,并且能够提供最高 9V的输出电压。

HT8905具有可外部调节的限流保护功能,不仅可保护芯片过流,亦可有效防止电池被拉死。

HT8905外围精简,采用SOP8L-PP封装,使用 和测试简单,为便携式系统提供了高效的小尺 寸解决方案。

HT8905内置了9.5V的过压保护和过热关断保 护功能。





## ■ TERMINAL FUNCTION

	1	1	
Terminal No.	Name	I/O <sup>1</sup>	Description
1	EAOUT	0	Error amplifier output. Connect a 10nF capacity to GND. 误差放大器输出端,接10nF电容到地。
2,3	SW	Р	The switching node pin of the converter. 升压整流管输入端。
4	VIN	Ι	IC power supply input. 芯片电源输入端
5	EN	Ι	Enable logic input. Logic high level enables the device. Logic low level disables the device. 芯片使能端,高电平使能,低电平关断。
6	FB	Ι	Regulator Feedback Input. 升压调节反馈输入端。
7	POUT	Ι	Boost Converter voltage detect pin. 升压输出检测端。
8	ILIM	0	Adjustable switch peak current limit. An external resister paralleled with a 1nF capacitor should be connected between this pin and the GND pin. 最大限流值设置端,外接电阻并联1nF到地。
0	GND	G	Power ground. Also provides thermal connection from the device to the board. A matching ground pad should be provided on the PCB and the device connected to it via solder. 芯片地,同时提供器件向板级散热的路径。PCB 板上需要留有足够的铺地露铜与之良好焊接。

<sup>&</sup>lt;sup>1</sup> I: Input; O: Output; G: Ground; P: Power



#### SPECIFICATIONS<sup>1</sup>

### • Absolute Maximum Ratings<sup>\*2</sup>

	PARAMETER	Symbol	MIN	MAX	UNIT
	SW	,	-0.3	11	N/
Voltage range	VIN, VOUT		-0.3	10	V
Operating temperat	ure range	TA	-40	85	°C
Operating junction	temperature range	TJ	-40	150	°C
Storage temperatur	e range	T <sub>STG</sub>	-50	150	°C

#### • Recommended Operating Conditions

PARAMETER	Symbol	CONDITION	MIN	TYP	MAX	UNIT
IC power supply voltage range	V <sub>IN</sub>		2.5		9	V
Output voltage range	Vout		2.5		9	V
Inductance, effective value	L		2.2	4.7	10	μH
Input capacitance, effective value	Cı			470		μF
Output capacitance, effective value	Co			470		μF
Operating temperature	Ta		-40	25	85	°C
Operating junction temperature	TJ		-40		125	°C

#### • Electrical Characteristics<sup>-3</sup>

Condition: Ta =  $25^{\circ}$ C, V<sub>IN</sub> = 2.7V-8.5V, V<sub>POUT</sub>=4.5-9V, unless otherwise specified.

#### Power Supply

PARAMETER	Symbol	CONDITION	MIN	TYP	MAX	UNIT
Input power voltage range	V <sub>PIN</sub>		2.7		8.5	V
Under-voltage lockout	M	VIN rising	2.4			V
(UVLO) threshold	V <sub>IN_UVLO</sub>	VIN falling	2.1			V
VIN UVLO hysteresis	$V_{\text{IN}_{\text{HYS}}}$			300		mV
Quisseent surrent	$I_{Q_{VIN}}$	V <sub>IN</sub> = 3.7V, V <sub>POUT</sub> = 7.5V, no SW		0.5		mA
Quiescent current	IQ_POUT	switching		2.5		mA
Shutdown current	I <sub>SD</sub>	IC disabled, $V_{IN}$ = 3.7 V, without current consumed by FB resistors.		1		uA

#### Input and Output

PARAMETER	Symbol	CONDITION	MIN	TYP	MAX	UNIT
EN high threshold voltage	$V_{\text{ENH}}$		1.5			V
EN low threshold voltage	V <sub>ENL</sub>				0.4	V
EN internal pull-down resistance	Ren			300		kΩ
EN delay time	$T_{delay}$			4.5		ms
Output voltage range	V <sub>OUT</sub>		V <sub>IN</sub>		9	V
Output overvoltage protection	V <sub>OVP</sub>			9.5		V
Reference voltage at	V <sub>REF</sub>	At light load		1.24		V
the FB pin	V REF	Out-off light load		1.2		V

<sup>&</sup>lt;sup>1</sup> Depending on parts and PCB layout, characteristics may be changed.

<sup>&</sup>lt;sup>2</sup> Stresses beyond those listed under absolute maximum ratings may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under recommended operating conditions is not implied. Exposure to absolute–maximum–rated conditions for extended periods may affect device reliability.
<sup>3</sup> Depending on parts and pattern layout, characteristics may be changed.



#### Other characteristics

PARAMETER	Symbol	CONDITION	MIN	TYP	MAX	UNIT
POWER SWITCH		•	•	•		
MOSFET on-resistance	R <sub>DS(on)</sub>			60		mΩ
CURRENT LIMIT		·				
Peak switch current limit	I <sub>LIM</sub>	R <sub>ILIM</sub> = 510 kΩ		8		A
Boost converter start-up limit				4		A
Reference voltage at the ILIM pin	VILIM			1.24		V
SWITCHING FREQUEN	ICY					
Switching frequency	<i>f</i> sw			650		kHz
Protection		·				•
Thermal shutdown threshold	T <sub>SD</sub>			150		°C
Thermal shutdown hysteresis	T <sub>SD_HYS</sub>			20		°C



## ■ TYPICAL OPERATING CHARACTERISTICS

深圳市永阜康科技有限公司

Condition:  $L = 4.7 \mu H$ , D=2\*SS54, FB=120k+20k//1nF,  $R_{ILIM} = 510k//1nF$ ,  $C_{EAOUT} = 10nF$ ,

VIN=3.7V, Input Capacitor = Output Capacitor = 1uF//10uF//470uF, otherwise specified.











## ■ APPLICATION INFORMATION

#### 1. Feature Description

#### 1.1 Operation

The non-synchronous boost converter HT8905 operates at a quasi-constant frequency pulse width modulation (PWM) in moderate to heavy load condition. The switching frequency is around 650kHz. It is optimized for single Li-Ion and Li-polymer battery powered products, in a wide range of wireless speakers, power bank and other portable devices. The converter integrates  $60-m\Omega$  power switches and is capable of delivering up to 3-A output current for 3.7V to 7.5V conversion.

#### 1.2 Current Limit Program

A resistor paralleled with a capacitor between ILIM and GND pin determines the peak switch current. The resistor value should be not smaller than 500kohm, so that the current limit will be set below 9A.

HT8905 为异步升压转换 IC。当处于轻载 状态,HT8905 工作在非连续的 PFM 模式;当 负载加重,工作于连续的 PWM 模式,PWM 开 关频率约为 650kHz。HT8905 适用于单节锂电 或者双节锂电的宽电压范围应用。HT8905 内置 60m Ω MOS 开关,可以从 3.7V 升压到 7.5V 并提供 3A 稳定输出。

ILIM, 输入限流设定端, 接一个电阻和一个 电容到地。一般电阻不小于 500k,这样峰值电流 不超 9A。



#### Figure 2 ILIM Terminal Configuration

Recommended values for R<sub>ILIM</sub> and C<sub>ILIM</sub> are shown in the . 推荐 R<sub>ILIM</sub> 和 C<sub>ILIM</sub> 如下表。following table.

Table. 1	Recommended	values for	RILIM and CILIM
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Peak current value (A)	R <sub>ILIM</sub> (ohm)	C <sub>ILIM</sub> (ohm)
8A	510k	1nF
6.8A	560k	1nF
5.8A	620k	1nF
4.5A	680k	1nF

#### 1.3 Enable (EN pin)

When the EN pin is pulled into logic low (below 0.4V), the HT8905 goes into the shutdown mode and stops switching. Only when EN pin is pulled into logic high (above 1.5V), the HT8905 works.

当 EN 脚输入低电平(<0.4V), HT8905 进入 低功耗休眠状态。只有当 EN 脚输入高电平 (>1.5V), HT8905 才正常工作。



#### 1.4 Output Voltage Setting (FB pin)

The output voltage is set by an external resistor divider ( $R_{UP}$ ,  $R_{DN}$  in the Typical Application Circuit). Make sure that a 1nF capacitor should be paralleled with  $R_{DN}$ . To get the output voltage VOUT, the Value of  $R_{UP}$  and  $R_{DN}$  can be calculated as following. Some typical output voltages can be set as the following table.

升压输出电压由 FB 上分压电阻(Rp/Rd)决定。 请并联 1nF 电容在 Rd 电阻上。升压值 POUT 由下公式决定:

$$V_{OUT} = V_{REF} \times (1 + \frac{R_{UP}}{R_{DN}}),$$

where  $V_{REF}{\approx}1.24V$  at light load,and  $V_{REF}{\approx}1.2V$  at heavy load

Vou	г (V)	R <sub>UP</sub> (ohm)	R <sub>DN</sub> (ohm)
Light load	Heavy load		
9	8.7	150k	24k
8.7	8.4	120k	20k
8	7.8	120k	22k
7.6	7.4	120k	23.2k

Table. 3 Internal input resistors and feedback resistors

#### **1.5 Inductor Selection (SW pin)**

Because the selection of the inductor affects the power supply's steady state operation, transient behavior, loop stability, and boost converter efficiency, the inductor is the most important component in switching power regulator design. Three most important specifications to the performance of the inductor are the inductor value, DC resistance, and saturation current.

To be simplified, the inductor value can be set between  $2.2 \text{uH} \sim 6.8 \text{uH}$  which can be used in most cases.

The rated current, especially the saturation current should be larger than the peak current during the whole operation. The peak current can be calculated as follows.

$$I_{Lpeak} = I_{DC} + \frac{I_{PP}}{2}$$

$$I_{DC} = \frac{V_{OUT} \times I_{OUT}}{V_{IN} \times \eta}$$

$$I_{PP} = \frac{1}{L \times (\frac{1}{V_{OUT} - V_{IN}} + \frac{1}{V_{IN}}) \times f_{SW}}$$

Boost converter efficiency is affected significantly by the inductor's DC resistance (DCR), equivalent series resistance (ESR) at the switching frequency, and the core loss. An inductor with lower DCR and ESR would increase the efficiency significantly.

The inductor should be placed as close as possible to the SW pin

电感的参数会影响电源的稳定性、转换效 率以及环路稳定性。电感值、DC 电阻、饱和电 流为电感的 3 个重要参数指标。

简单来说,电感值可以从 2.2uH 到 6.8uH 之间选择,可以满足绝大多数应用。

电感的饱和电流,需要大于应用中的最大 峰值电流。峰值电流的计算如下:

电感的 DCR 严重影响升压转换效率,在开关当中,等效电阻发热,损失效率。低 DCR 的电感可有效改善升压效率。

电感摆放位置请尽量靠近 SW 管脚。



For good input voltage filtering and small voltage ripple (less than 100mV is required), we recommend low-ESR capacitors of 1uF//10uF//470uF ("//" represents paralleled) be placed as close as possible to the inductor.

The  $V_{\rm IN}$  pin is the power supply for the HT8905, a 1uF ceramic capacitor should be placed as close as possible to the  $V_{\rm IN}$  pin..

### 1.7 Output Capacitor Selection (VOUT pin)

To be simplified, we recommend low-ESR capacitors of 1 uF//10 uF//470 uF ("//" represents paralleled) be placed as close as possible to DIODE for small output voltage ripple.

Capacitors can lose most of their capacitance at rated voltage. Therefore, leave margin on the voltage rating to ensure adequate effective capacitance.

#### 1.8 Diode Selection

Schottky diode with fast recovery times and low forward voltages are recommended. Ensure the diode average and peak current rating exceed the average output current and peak inductor current. In addition, the diode's reverse breakdown voltage must exceed the output voltage.

选择低ESR的输入滤波电容组合可有效减 小输入纹波,我们推荐470uF//10uF//1uF的输入 滤波电容组合。滤波电容尽量靠近电感。

VIN 管脚为逻辑电源输入管脚,摆放 1uF 陶瓷电容滤波。

选择低ESR的输出滤波电容组合可有效减小输出纹波,我们推荐470uF//10uF//1uF的输出滤波电容组合。滤波电容尽量靠近肖特基二极管输出。

建议选用快恢复时间、低正向导通电压的肖特基 二极管。确保二极管的平均电流和峰值电流参数 大于实际应用中平均电流和峰值电流。另外,二 极管的反向雪崩电压必须大于输出电压。

#### 1.9 EAOUT pin

The HT8905 requires external compensation for the stability of boost converter. The EAOUT pin is the output of the internal error amplifier. An external ceramic capacitors 10nF is connected from the EAOUT pin to GND.

#### 1.10 Protection Function

#### Under-voltage Lockout (UVLO)

The UVLO circuit prevents the device from malfunctioning at low input voltage and the battery from excessive discharge. It disables the device from switching when the falling voltage at the VIN pin trips the UVLO threshold  $V_{IN\_UVLO}$ , which is typically 2.4V. The device starts operating when the rising voltage at the VIN pin is 300mV above the  $V_{IN\_UVLO}$ .

#### **Over-voltage Protection**

If the output voltage at the VOUT pin is detected above 9.5V (typical value), the HT8905 stops switching immediately until the voltage at the VOUT pin drops the hysteresis value lower than the output overvoltage protection threshold. This function prevents overvoltage on the output and secures the circuits connected to the output from excessive overvoltage.

HT8905需要外部补偿电路来确保正常工作, 在EAOUT管脚上并联一个10nF电容到地。

HT8905内含欠压保护电路,来防止输入电 压过低或者电池过放。欠压状态,HT8905处于 关断状态。VIN启动电压为2.4V,有300mV迟滞。

HT8905 内含过压保护电路。但 VOUT 电压大于 9.5V, IC 立即停止开关工作。当 VOUT 电压下降低于迟滞电压后,HT8905 重新开始工作。过压保护功能保证输出电压的安全性。



#### Thermal Shutdown

A thermal shutdown is implemented to prevent damages due to excessive heat and power dissipation. Typically, the thermal shutdown happens at a junction temperature of 150°C. When the thermal shutdown is triggered, the device stops switching until the junction temperature falls below typically 130°C, then the device starts switching again.

#### 2. Application Notes

#### 2.1 Radiated EMI Reduction

(1) Minimize High di/dt Path loop area

EMI Starts off from high di/dt loops. The high di/dt critical path locates as the thick circle showed in the application. The output capacitor should be placed as close to the DIODE as possible resulting in minimum area of the high di/dt loop.

(2) PCB Trace and Ground Plane

High trace inductance leads to poor radiation EMI. The inductance of a PCB trance is a function of its length and width. So, increase the trace width and decrease the trace length will significantly decrease the radiation EMI.

Meanwhile, good designed ground planes will help decrease the radiation EMI too:

- Placing a solid ground plane with minimum distance to the critical trace;
- Wider and bigger ground plane result in smaller signal trace inductance;
- Thinner insulation thickness between the ground plane and the signal traces also results in smaller inductance;
- (3) RC Snubber

Adding an RC snubber across the SW pin and the power ground can help reduce the radiation EMI levels. The RC snubber should be placed as close as possible to the switching node and the power ground. HT8905内含过温保护功能,保护IC因温度太 高而损坏。当HT8905内部温度达到150℃,IC立 即停止工作。当温度降低低于130℃,IC重新开 始正常工作。

EMI 改善措施:

减小 di/dt 环路面积。大电流路径在应用图 当中以加粗标出。输出滤波电容尽量靠近整流二 极管。

PCB 走线的寄生电感会恶化 EMI,影响寄 生电感的因素是走线的长度和宽度。所以,增加 大电流路径的走线宽度,减小走线长度可有效改 善 EMI。

好的地平面设计,同样帮助减小 EMI:

完整的地平面,可以减小电流回路以及寄 生电感。

RC 吸收电路,在 SW 上增加一个 RC 吸收 电路,可较小 SW 上振铃来改善 EMI。



Figure 1 Placement of RC Snubber

RC 吸收电路的选择如下:

The aim of the snubber resistor RS is to add sufficient damping to the parasitic resonant circuit. The value of RS depends on the desired damping factor and the parasitic inductor IP and parasitic capacitor CP of the circuit:

$$\mathbf{R}_{S} = \frac{1}{\xi} \times \sqrt{\frac{L_{P}}{C_{P}}}$$

Where  $\xi$  is the damping factor, normally can range from 0.5 to 1.



- Measure the original ringing frequency f<sub>RING</sub>;
- Add some small capacitance from switch node to ground. Keep increasing capacitance until the ringing frequency is 50% of the original ringing frequency  $f_{RING}$ , and the capacitance is  $C_S$ ,  $C_P = 1/(3C_S)$ ;
- $L_P = \frac{1}{C_P \times (2\pi \times f_{RING})^2}$

To be simplified, a resistor of 10hm ( $R_S$ ) and a capacitor of 2.2nF ( $C_S$ ) can be used. However, notice that larger  $C_S$  results in higher power loss.

(4) Radiation from Cables

A longer input or output cables result in poor radiation EMI. So, make the length of input cable and output cable very close to the real application.

#### 2.2 Layout Guidelines

1. Minimize the length and area of all traces connected to the SW pin, and always use a ground plane under the switching regulator to minimize interplane coupling.

2. The input capacitor needs to be close to inductor L, and GND pin in order to reduce the input supply ripple. The output capacitor needs to be close to DIODE and GND pin in order to reduce the output supply ripple.

3. The layout should also be done with well consideration of the thermal as this is a high-power density device. A thermal pad that improves the thermal capabilities of the package should be soldered to the large ground plate, using thermal vias underneath the thermal pad. 一般来说,建议使用1Ω电阻和2.2nF电容。 请记住,电容越大,静态消耗越大。

请尽量选择较短的输入与输出走线来改下 EMI。

- 减小 SW 走线路径和面积,在 SW 底部铺 一块完整的地,来减小耦合。
- 输入滤波电容尽量靠近电感和输入电源的 地。输出滤波电容尽量靠近二极管整流输出。
- **PCB** 布局同时考虑热耗散。芯片底部大的 裸焊盘可有效改善散热,同时增加过孔帮助散热。



## 3. Typical Application Circuit





4. PCB Layout









## PACKAGE OUTLINE

## SOP8-PP(EXP PAD) PACKAGE OUTLINE DIMENSIONS







字符	Dimensions I	n Millimeters	Dimension	s In Inches
	Min	Max	Min	Max
A	1.350	1. 750	0.053	0.069
A1	0. 050	0.150	0.002	0. 006
A2	1. 350	1. 550	0. 053	0. 061
b	0. 330	0. 510	0.013	0. 020
с	0.170	0. 250	0.007	0. 010
D	4. 700	5. 100	0. 185	0.200
D1	3. 202	3. 402	0. 126	0.134
E	3. 800	4.000	0.150	0.157
E1	5. 800	6.200	0.228	0.244
E2	2. 313	2.513	0.091	0. 099
е	1.27	0 (BSC)	0.05	D (BSC)
L	0. 400	1.270	0.016	0. 050
θ	0°	8°	0°	8°